Abstract

The present invention provides a silicon wafer wherein the occurrence of both slip dislocations and warpages during a device production process is suppressed, and a process for producing the same. The present silicon wafer contains BMDs with an octahedral shape, and of the BMDs present at a depth of not less than 50 μm from the surface of the silicon wafer, the density of BMDs with diagonal size of 10 nm to 50 nm is not less than $1 \times 10^{12}/cm^3$ and the density of BSFs is not more than $1 \times 10^{8}/cm^3$. The present silicon wafer should have an interstitial oxygen concentration of not less than 4×10^{17} atoms/cm^3 to not more than 6×10^{17} atoms/cm^3, and the density of BMDs with diagonal size of not less than 200 nm is not more than $1 \times 10^{7}/cm^3$.